

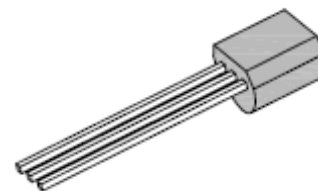
Small Signal High Voltage Transistor (NPN)

Features

- High Voltage NPN Transistor for General Purpose and Telephony Applications

Mechanical Data

Case:	TO-92, Plastic Package
Terminals:	Solderable per MIL-STD-202G, Method 208
Weight:	0.18 gram



TO-92



Maximum Ratings ($T_{Ambient}=25^{\circ}C$ unless noted otherwise)

Symbol	Description	2N5551	Unit	Conditions
V_{CBO}	Collector-Base Voltage	180	V	
V_{CEO}	Collector-Emitter Voltage	160	V	
V_{EB0}	Emitter-Base Voltage	6.0	V	
I_C	Collector Current Continuous	600	mA	
P_D	Power Dissipation at $T_a=25^{\circ}C$	625	mW	
	Derate above $25^{\circ}C$	5.0	mW/ $^{\circ}C$	
R_{θJC}	Junction to Case	125	$^{\circ}C/W$	Measured with the device soldered into a typical printed circuit board
R_{θJA}	Junction to Ambient	357		
T_J, T_{STG}	Operation and Storage Junction Temperature Range	-55 to +150	$^{\circ}C$	

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Electrical Characteristics ($T_{Ambient}=25^{\circ}\text{C}$ unless noted otherwise)

Symbol	Description	Min.	Max.	Unit	Conditions
h_{FE}*	D.C. Current Gain	80	-		V _{CE} =5V, I _C =1mA
		80	400		V _{CE} =5V, I _C =10mA
		50	-		V _{CE} =5V, I _C =50mA
I_{CBO}	Collector Cut-Off Current	-	50	nA	V _{CB} =120V, I _E =0
I_{EBO}	Emitter Cut-Off Current	-	50	nA	V _{EB} =4V, I _C =0
V_{CE(Sat)}*	Collector Emitter Saturation Voltage	-	0.15	V	I _C =10mA, I _B =1mA
		-	0.2		I _C =50mA, I _B =5mA
V_{BE(Sat)}*	Base Emitter Saturation Voltage	-	1.0	V	I _C =10mA, I _B =1mA
			1.0		I _C =50mA, I _B =5mA
V_{CB0}	Collector-Base Voltage	180	-	V	I _C =100μA, I _E =0
V_{CEO}	Collector-Emitter Voltage	160	-	V	I _C =1mA, I _B =0
V_{EB0}	Emitter-Base Voltage	6.0	-	V	I _E =10μA, I _C =0
f_t	Transition Frequency	100	300	MHz	V _{CE} =10V, I _C =10mA, f=100MHz
C_{ob}	Output Capacitance	-	6.0	pF	V _{CB} =10V, f=1.0MHz, I _E =0

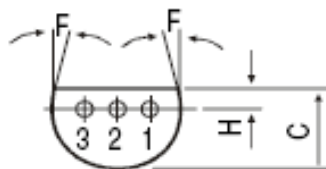
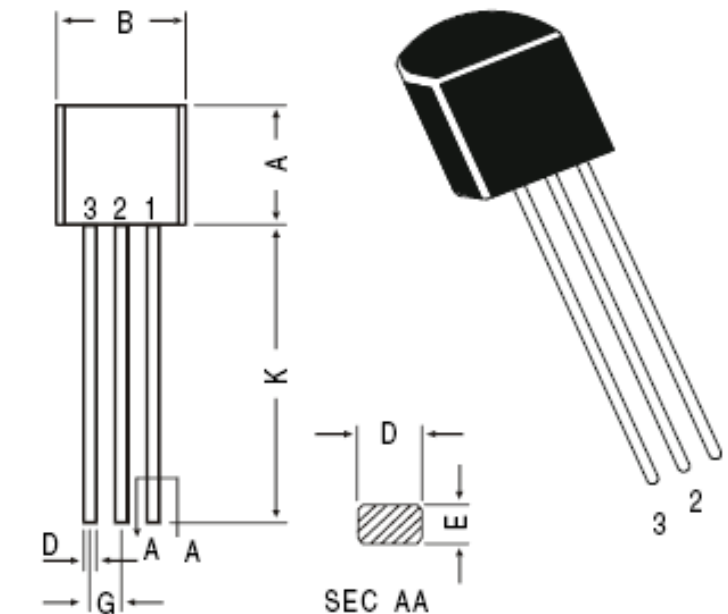
*Pulse Test: Pulse Width=300μs, Duty Cycle=2%

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Dimensions in mm

TO-92



PIN CONFIGURATION
1. COLLECTOR
2. BASE
3. EMITTER

All dimensions in mm.

DIM	MIN.	MAX.
A	4.33	4.83
B	4.33	4.83
C	3.36	3.76
D	0.36	0.56
E	0.36	0.56
F	5 DEG	
G	1.14	1.40
H	1.14	1.53
K	12.70	—

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